NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 1517-025M** is Designed for Satellite communications applications in the 1620 to 1660 MHz range.

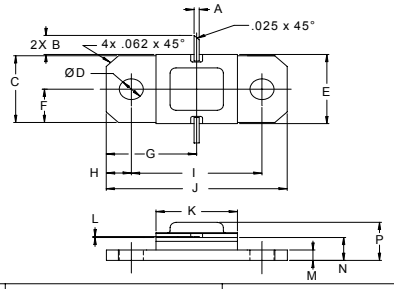
FEATURES:

- Internal Input/Output Matching Networks
- P_G = 8.5 dB at 25 W/1.5 – 1.7 GHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2.5 A
V_{CC}	30 V
P_{DISS}	45 W @ $T_C \leq 100$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	3.3 °C/W

PACKAGE STYLE .400 2NL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F	.193 / 4.90	
G	.450 / 11.43	
H	.125 / 3.18	
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

COMMON BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 8.0 mA	45			V
BV_{EBO}	I_E = 8.0 mA	3.0			V
I_{CBO}	V_{CE} = 28 V			2.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.6 A	15		150	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			80	pF
P_G	V_{CC} = 28 V P_{OUT} = 25 W f = 1620 – 1660 MHz	8.5			dB
η_C	P_{IN} = 3.5 W	55	58		%